## NLAST44599

## Low Voltage Single Supply Dual DPDT Analog Switch

The NLAST44599 is an advanced CMOS dual-independent DPDT (double pole-double throw) analog switch, fabricated with silicon gate CMOS technology. It achieves high-speed propagation delays and low ON resistances while maintaining CMOS low-power dissipation. This DPDT controls analog and digital voltages that may vary across the full power-supply range (from $\mathrm{V}_{\mathrm{CC}}$ to GND).

The device has been designed so the ON resistance ( $\mathrm{R}_{\mathrm{ON}}$ ) is much lower and more linear over input voltage than $\mathrm{R}_{\mathrm{ON}}$ of typical CMOS analog switches.

The channel-select input structure provides protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. This input structure helps prevent device destruction caused by supply voltage - input/output voltage mismatch, battery backup, hot insertion, etc.

The NLAST44599 can also be used as a quad 2-to-1 multiplexerdemultiplexer analog switch with two Select pins that each controls two multiplexer-demultiplexers.

- Select Pins Compatible with TTL Levels
- Channel Select Input Overvoltage Tolerant to 5.5 V
- Fast Switching and Propagation Speeds
- Break-Before-Make Circuitry
- Low Power Dissipation: $\mathrm{I}_{\mathrm{CC}}=2 \mu \mathrm{~A}(\mathrm{Max})$ at $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$
- Diode Protection Provided on Channel Select Input
- Improved Linearity and Lower ON Resistance over Input Voltage
- Latch-up Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V;

Machine Model > 100 V

- Chip Complexity: 158 FETs
- Pb-Free Packages are Available


## ON Semiconductor ${ }^{\circledR}$

http://onsemi.com

MARKING DIAGRAMS


$$
\begin{array}{ll}
\text { A } & =\text { Assembly Location } \\
\text { L } & =\text { Wafer Lot } \\
\text { Y } & =\text { Year } \\
\text { W } & =\text { Work Week } \\
\text { - } & \text { Pb-Free Package }
\end{array}
$$

(Note: Microdot may be in either location)

ORDERING INFORMATION
See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.


| Select AB or CD | ON Channel |
| :---: | :---: |
| L | NC to COM |
| H | NO to COM |


Figure 2. IEC Logic Symbol

Figure 1. Logic Diagram

MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
| :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {CC }}$ | Positive DC Supply Voltage | -0.5 to +7.0 | V |
| $V_{\text {IS }}$ | Analog Input Voltage ( $\mathrm{V}_{\text {NO }}$ or $\mathrm{V}_{\text {COM }}$ ) | $-0.5 \leq \mathrm{V}_{\text {IS }} \leq \mathrm{V}_{\text {CC }}+0.5$ | V |
| $\mathrm{V}_{\text {IN }}$ | Digital Select Input Voltage | $-0.5 \leq \mathrm{V}_{1} \leq+7.0$ | V |
| $\mathrm{I}_{\text {IK }}$ | DC Current, Into or Out of Any Pin | $\pm 50$ | mA |
| $\mathrm{P}_{\mathrm{D}}$ | $\begin{array}{lr}\text { Power Dissipation in Still Air } & \text { QFN-16 } \\ \text { TSSOP-16 }\end{array}$ | $\begin{aligned} & 800 \\ & 450 \end{aligned}$ | mW |
| TSTG | Storage Temperature Range | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{L}}$ | Lead Temperature, 1 mm from Case for 10 Seconds | 260 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{J}}$ | Junction Temperature Under Bias | +150 | ${ }^{\circ} \mathrm{C}$ |
| MSL | Moisture Sensitivity | Level 1 |  |
| $\mathrm{F}_{\mathrm{R}}$ | Flammability Rating Oxygen Index: 30\% - 35\% | UL-94-VO (0.125 in) |  |
| $\mathrm{V}_{\text {ESD }}$ | ESD Withstand Voltage Human Body Model (Note 1) <br> Machine Model (Note 2) <br> Charged Device Model (Note 3) | $\begin{gathered} 2000 \\ 100 \\ 1000 \end{gathered}$ | V |
| ILATCH-UP | Latch-Up Performance $\quad$ Above $\mathrm{V}_{\mathrm{CC}}$ and Below GND at 125 ${ }^{\circ} \mathrm{C}$ (Note 4) | $\pm 300$ | mA |
| $\theta_{\text {JA }}$ | Thermal Resistance $\begin{array}{r}\text { QFN-16 } \\ \text { TSSOP-16 }\end{array}$ | $\begin{gathered} \hline 80 \\ 164 \end{gathered}$ | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Tested to EIA/JESD22-A114-A.
2. Tested to EIA/JESD22-A115-A.
3. Tested to JESD22-C101-A.
4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit |
| :--- | :--- | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | DC Supply Voltage | 2.0 | 5.5 | V |
| $\mathrm{~V}_{\mathrm{IN}}$ | Digital Select Input Voltage | GND | 5.5 | V |
| $\mathrm{~V}_{\mathrm{IS}}$ | Analog Input Voltage (NC, NO, COM) | GND | $\mathrm{V}_{\mathrm{CC}}$ | V |
| $\mathrm{T}_{\mathrm{A}}$ | Operating Temperature Range | -55 | +125 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{t}_{\mathrm{r}}, \mathrm{t}_{\mathrm{f}}$ | Input Rise or Fall Time, SELECT |  | $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V} \pm 0.3 \mathrm{~V}$ | 0 |
|  |  | $\mathrm{~V}_{\mathrm{CC}}=5.0 \mathrm{~V} \pm 0.5 \mathrm{~V}$ | 0 | 100 |
| 20 | $\mathrm{~ns} / \mathrm{V}$ |  |  |  |

## DEVICE JUNCTION TEMPERATURE VERSUS

TIME TO 0.1\% BOND FAILURES

| Junction <br> Temperature ${ }^{\circ} \mathbf{C}$ | Time, Hours | Time, Years |
| :---: | :---: | :---: |
| 80 | $1,032,200$ | 117.8 |
| 90 | 419,300 | 47.9 |
| 100 | 178,700 | 20.4 |
| 110 | 79,600 | 9.4 |
| 120 | 37,000 | 4.2 |
| 130 | 17,800 | 2.0 |
| 140 | 8,900 | 1.0 |



Figure 3. Failure Rate vs. Time Junction Temperature

DC CHARACTERISTICS - Digital Section (Voltages Referenced to GND)

| Symbol | Parameter | Condition | V cc | Guaranteed Limit |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | $-55^{\circ} \mathrm{C}$ to $25^{\circ} \mathrm{C}$ | $<85^{\circ} \mathrm{C}$ | $<125^{\circ} \mathrm{C}$ |  |
| $\mathrm{V}_{\mathrm{IH}}$ | Minimum High-Level Input Voltage, Select Inputs |  | $\begin{aligned} & \hline 3.0 \\ & 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & 2.0 \\ & 2.0 \\ & 2.0 \end{aligned}$ | $\begin{aligned} & 2.0 \\ & 2.0 \\ & 2.0 \end{aligned}$ | $\begin{aligned} & 2.0 \\ & 2.0 \\ & 2.0 \end{aligned}$ | V |
| VIL | Maximum Low-Level Input Voltage, Select Inputs |  | $\begin{aligned} & \hline 3.0 \\ & 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & 0.5 \\ & 0.8 \\ & 0.8 \\ & \hline \end{aligned}$ | $\begin{aligned} & 0.5 \\ & 0.8 \\ & 0.8 \end{aligned}$ | $\begin{aligned} & 0.5 \\ & 0.8 \\ & 0.8 \end{aligned}$ | V |
| $\mathrm{I}_{\mathrm{N}}$ | Maximum Input Leakage Current | $\mathrm{V}_{\mathrm{IN}}=5.5 \mathrm{~V}$ or GND | 5.5 | $\pm 0.2$ | $\pm 2.0$ | $\pm 2.0$ | $\mu \mathrm{A}$ |
| IOFF | Power Off Leakage Current, Select Inputs | $\mathrm{V}_{\mathrm{IN}}=5.5 \mathrm{~V}$ or GND | 0 | $\pm 10$ | $\pm 10$ | $\pm 10$ | $\mu \mathrm{A}$ |
| ICC | Maximum Quiescent Supply Current | Select and $\mathrm{V}_{\text {IS }}=\mathrm{V}_{\mathrm{CC}}$ or GND | 5.5 | 4.0 | 4.0 | 8.0 | $\mu \mathrm{A}$ |

DC ELECTRICAL CHARACTERISTICS - Analog Section

| Symbol | Parameter | Condition | $\mathrm{V}_{\mathrm{cc}}$ | Guaranteed Limit |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | $-55^{\circ} \mathrm{C}$ to $25^{\circ} \mathrm{C}$ | $<85^{\circ} \mathrm{C}$ | $<125^{\circ} \mathrm{C}$ |  |
| $\mathrm{R}_{\text {ON }}$ | Maximum "ON" Resistance (Figures 17 - 23) | $\begin{aligned} & \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{IL}} \text { or } \mathrm{V}_{\mathrm{IH}} \\ & \mathrm{~V}_{\mathrm{IS}}=\mathrm{GND} \text { to } \mathrm{V}_{\mathrm{CC}} \\ & \mathrm{I}_{\mathrm{IN}} \leq 10.0 \mathrm{~mA} \end{aligned}$ | $\begin{aligned} & 2.5 \\ & 3.0 \\ & 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & 85 \\ & 45 \\ & 30 \\ & 25 \end{aligned}$ | $\begin{aligned} & 95 \\ & 50 \\ & 35 \\ & 30 \end{aligned}$ | $\begin{gathered} 105 \\ 55 \\ 40 \\ 35 \end{gathered}$ | $\Omega$ |
| RFLAT (ON) | ON Resistance Flatness <br> (Figures 17-23) | $\begin{aligned} & \hline \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{IL}} \text { or } \mathrm{V}_{\mathrm{IH}} \\ & \mathrm{I}_{\mathrm{IN}} \leq 10.0 \mathrm{~mA} \\ & \mathrm{~V}_{\mathrm{IS}}=1 \mathrm{~V}, 2 \mathrm{~V}, 3.5 \mathrm{~V} \\ & \hline \end{aligned}$ | 4.5 | 4 | 4 | 5 | $\Omega$ |
| $\mathrm{I}_{\text {NC(OFF) }}$ INO(OFF) | NO or NC Off Leakage Current (Figure 9) | $\begin{aligned} & \hline \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{IL}} \text { or } \mathrm{V}_{\mathrm{IH}} \\ & \mathrm{~V}_{\mathrm{NO}} \text { or } \mathrm{V}_{\mathrm{NC}}=1.0 \mathrm{~V}_{\mathrm{COM}} 4.5 \mathrm{~V} \end{aligned}$ | 5.5 | 1 | 10 | 100 | nA |
| $\mathrm{I}_{\text {COM(ON }}$ | COM ON Leakage Current (Figure 9) | $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{IL}} \text { or } \mathrm{V}_{\mathrm{IH}}$ <br> $\mathrm{V}_{\mathrm{NO}} 1.0 \mathrm{~V}$ or 4.5 V with $\mathrm{V}_{\mathrm{NC}}$ floating or <br> $\mathrm{V}_{\mathrm{NO}} 1.0 \mathrm{~V}$ or 4.5 V with $\mathrm{V}_{\mathrm{NO}}$ floating <br> $\mathrm{V}_{\text {COM }}=1.0 \mathrm{~V}$ or 4.5 V | 5.5 | 1 | 10 | 100 | nA |

AC ELECTRICAL CHARACTERISTICS (Input $t_{r}=t_{f}=3.0 \mathrm{~ns}$ )

| Symbol | Parameter | Test Conditions | $\begin{aligned} & \mathrm{V}_{\mathrm{Cc}} \\ & (\mathrm{~V}) \end{aligned}$ | $\mathrm{V}_{\mathrm{IS}}$ <br> (V) | Guaranteed Maximum Limit |  |  |  |  |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  | $-55^{\circ} \mathrm{C}$ to $25^{\circ} \mathrm{C}$ |  |  | $<85^{\circ} \mathrm{C}$ |  | $<125^{\circ} \mathrm{C}$ |  |  |
|  |  |  |  |  | Min | Typ* | Max | Min | Max | Min | Max |  |
| $\mathrm{t}_{\mathrm{ON}}$ | Turn-On Time (Figures 12 and 13) | $\mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF}$ <br> (Figures 5 and 6) | $\begin{aligned} & 2.5 \\ & 3.0 \\ & 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & 2.0 \\ & 2.0 \\ & 3.0 \\ & 3.0 \end{aligned}$ | $\begin{aligned} & 5 \\ & 5 \\ & 2 \\ & 2 \end{aligned}$ | $\begin{gathered} 23 \\ 16 \\ 11 \\ 9 \end{gathered}$ | $\begin{aligned} & 35 \\ & 24 \\ & 16 \\ & 14 \end{aligned}$ | $\begin{aligned} & 5 \\ & 5 \\ & 2 \\ & 2 \end{aligned}$ | $\begin{aligned} & 38 \\ & 27 \\ & 19 \\ & 17 \end{aligned}$ | $\begin{aligned} & 5 \\ & 5 \\ & 2 \\ & 2 \end{aligned}$ | $\begin{aligned} & 41 \\ & 30 \\ & 22 \\ & 20 \end{aligned}$ | ns |
| toff | Turn-Off Time <br> (Figures 12 and 13) | $\mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF}$ <br> (Figures 5 and 6) | $\begin{aligned} & 2.5 \\ & 3.0 \\ & 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & 2.0 \\ & 2.0 \\ & 3.0 \\ & 3.0 \end{aligned}$ | $\begin{aligned} & 1 \\ & 1 \\ & 1 \\ & 1 \end{aligned}$ | $\begin{aligned} & 7 \\ & 5 \\ & 4 \\ & 3 \end{aligned}$ | $\begin{gathered} 12 \\ 10 \\ 6 \\ 5 \end{gathered}$ | $\begin{aligned} & 1 \\ & 1 \\ & 1 \\ & 1 \end{aligned}$ | $\begin{gathered} 15 \\ 13 \\ 9 \\ 8 \end{gathered}$ | $\begin{aligned} & 1 \\ & 1 \\ & 1 \\ & 1 \end{aligned}$ | $\begin{aligned} & 18 \\ & 16 \\ & 12 \\ & 11 \end{aligned}$ | ns |
| $\mathrm{t}_{\text {BBM }}$ | Minimum Break-Before-Make Time | $\begin{aligned} & \mathrm{V}_{\mathrm{IS}}=3.0 \mathrm{~V} \text { (Figure 4) } \\ & \mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} \end{aligned}$ | $\begin{aligned} & \hline 2.5 \\ & 3.0 \\ & 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & 2.0 \\ & 2.0 \\ & 3.0 \\ & 3.0 \end{aligned}$ | 1 1 1 1 | $\begin{gathered} \hline 12 \\ 11 \\ 6 \\ 5 \end{gathered}$ |  | 1 1 1 1 |  | 1 1 1 1 |  | ns |

*Typical Characteristics are at $25^{\circ} \mathrm{C}$.

|  |  | Typical @ 25, VCC = 5.0 V |  |
| :--- | :--- | :---: | :---: |
| $\mathrm{C}_{\mathrm{IN}}$ | Maximum Input Capacitance, Select Input | 8 |  |
| $\mathrm{C}_{\mathrm{NO} \text { or } \mathrm{C}_{\mathrm{NC}}}$ Analog I/O (Switch Off) | 10 | pF |  |
| $\mathrm{C}_{\mathrm{COM}}$ | Common I/O (Switch Off) | 10 |  |
| $\mathrm{C}_{(\mathrm{ON})}$ | Feedthrough (Switch On) | 20 |  |

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

| Symbol | Parameter | Condition | $\begin{gathered} \mathrm{v}_{\mathrm{Cc}} \\ \mathrm{v} \end{gathered}$ | Typical | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | $25^{\circ} \mathrm{C}$ |  |
| BW | Maximum On-Channel - 3 dB Bandwidth or Minimum Frequency Response <br> (Figure 11) | $\mathrm{V}_{\mathrm{IN}}=0 \mathrm{dBm}$ <br> $\mathrm{V}_{\text {IN }}$ centered between $\mathrm{V}_{\mathrm{CC}}$ and GND (Figure 7) | $\begin{aligned} & \hline 3.0 \\ & 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & \hline 145 \\ & 170 \\ & 175 \end{aligned}$ | MHz |
| $\mathrm{V}_{\text {ONL }}$ | Maximum Feedthrough On Loss | $\mathrm{V}_{\mathrm{IN}}=0 \mathrm{dBm}$ @ 100 kHz to 50 MHz <br> $\mathrm{V}_{\text {IN }}$ centered between $\mathrm{V}_{\mathrm{CC}}$ and GND <br> (Figure 7) | $\begin{aligned} & \hline 3.0 \\ & 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & \hline-3 \\ & -3 \\ & -3 \end{aligned}$ | dB |
| VISO | Off-Channel Isolation (Figure 10) | $\mathrm{f}=100 \mathrm{kHz} ; \mathrm{V}_{\mathrm{IS}}=1 \mathrm{VRMS}$ <br> $\mathrm{V}_{\text {IN }}$ centered between $\mathrm{V}_{\mathrm{CC}}$ and GND <br> (Figure 7) | $\begin{aligned} & \hline 3.0 \\ & 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & \hline-93 \\ & -93 \\ & -93 \\ & \hline \end{aligned}$ | dB |
| Q | Charge Injection Select Input to Common I/O (Figure 15) | $\begin{aligned} & \mathrm{V}_{\mathrm{IN}=} \mathrm{V}_{\mathrm{CC}} \text { to } \mathrm{GND}, \mathrm{~F}_{\mathrm{IS}}=20 \mathrm{kHz} \\ & \mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=3 \mathrm{~ns} \\ & \mathrm{R}_{\mathrm{IS}}=0 \Omega, C_{\mathrm{L}}=1000 \mathrm{pF} \\ & \mathrm{Q}=\mathrm{C}_{\mathrm{L}} * \Delta \mathrm{~V}_{\text {OUT }} \text { (Figure 8) } \end{aligned}$ | $\begin{aligned} & 3.0 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & 1.5 \\ & 3.0 \end{aligned}$ | pC |
| THD | Total Harmonic Distortion THD + Noise <br> (Figure 14) | $\begin{aligned} & \mathrm{F}_{\mathrm{IS}}=20 \mathrm{~Hz} \text { to } 100 \mathrm{kHz}, \mathrm{R}_{\mathrm{L}}=\text { Rgen }=600 \Omega, \\ & \mathrm{C}_{\mathrm{L}}=50 \mathrm{pF} \\ & \mathrm{~V}_{\text {IS }}=5.0 \mathrm{~V}_{\mathrm{PP}} \text { sine wave } \end{aligned}$ | 5.5 | 0.1 | \% |
| VCT | Channel to Channel Crosstalk | $\mathrm{f}=100 \mathrm{kHz}$; $\mathrm{V}_{\text {IS }}=1 \mathrm{~V}$ RMS <br> $\mathrm{V}_{\text {IN }}$ centered between $\mathrm{V}_{\mathrm{CC}}$ and GND <br> (Figure 7) | $\begin{aligned} & 5.5 \\ & 3.0 \end{aligned}$ | $\begin{aligned} & -90 \\ & -90 \end{aligned}$ | dB |

## NLAST44599



Figure 4. $\mathrm{t}_{\mathrm{BB}}$ (Time Break-Before-Make)


Figure 5. $\mathrm{t}_{\mathrm{ON}} / \mathrm{t}_{\mathrm{OFF}}$


Figure 6. $\mathrm{t}_{\mathrm{ON}} / \mathrm{t}_{\mathrm{OFF}}$


Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. $\mathrm{V}_{\text {ISO }}$, Bandwidth and $\mathrm{V}_{\text {ONL }}$ are independent of the input signal direction.
$\mathrm{V}_{\text {ISO }}=$ Off Channel Isolation $=20$ Log $\left(\frac{\mathrm{V}_{\text {OUT }}}{\mathrm{V}_{\text {IN }}}\right)$ for $\mathrm{V}_{\text {IN }}$ at 100 kHz
$\mathrm{V}_{\text {ONL }}=$ On Channel Loss $=20 \log \left(\frac{\mathrm{~V}_{\text {OUT }}}{\mathrm{V}_{\text {IN }}}\right)$ for $\mathrm{V}_{\text {IN }}$ at 100 kHz to 50 MHz
Bandwidth (BW) = the frequency 3 dB below $\mathrm{V}_{\mathrm{ONL}}$
$\mathrm{V}_{\mathrm{CT}}=$ Use $\mathrm{V}_{\text {ISO }}$ setup and test to all other switch analog input/outputs terminated with $50 \Omega$
Figure 7. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/ ${ }_{\text {ONL }}$


Figure 8. Charge Injection: (Q)


Figure 9. Switch Leakage vs. Temperature

## NLAST44599



Figure 10. Off-Channel Isolation


Figure 12. $\mathrm{t}_{\mathrm{ON}}$ and $\mathrm{t}_{\mathrm{OFF}}$ vs. $\mathrm{V}_{\mathrm{CC}}$ at $25^{\circ} \mathrm{C}$


Figure 14. Total Harmonic Distortion Plus Noise vs. Frequency


Figure 11. Typical Bandwidth and Phase Shift


Figure 13. $\mathrm{t}_{\mathrm{ON}}$ and $\mathrm{t}_{\text {OFF }}$ vs. Temp


Figure 15. Charge Injection vs. COM Voltage


Figure 16. $\mathrm{I}_{\mathrm{Cc}} \mathrm{vs}$. Temp, $\mathrm{V}_{\mathrm{Cc}}=3 \mathrm{~V}$ and 5 V


Figure 18. $\mathrm{R}_{\mathrm{ON}} \mathrm{vs}$ Temp, $\mathrm{V}_{\mathrm{CC}}=2.0 \mathrm{~V}$


Figure 20. RoN $_{\text {vs. }}$ Temp, $\mathrm{V}_{\mathrm{CC}}=3.0 \mathrm{~V}$


Figure 17. $\mathrm{R}_{\mathrm{ON}}$ vs. $\mathrm{V}_{\mathrm{CC}}, \mathrm{Temp}=25^{\circ} \mathrm{C}$


Figure 19. $\mathrm{R}_{\mathrm{ON}}$ vs. Temp, $\mathrm{V}_{\mathrm{CC}}=2.5 \mathrm{~V}$


Figure 21. $\mathrm{R}_{\mathrm{ON}}$ vs. Temp, $\mathrm{V}_{\mathrm{CC}}=4.5 \mathrm{~V}$


Figure 22. $\mathrm{R}_{\mathrm{ON}} \mathrm{vs}$. Temp, $\mathrm{V}_{\mathrm{CC}}=5.0 \mathrm{~V}$


Figure 23. R $_{\mathrm{ON}} \mathrm{vs}$. Temp, $\mathrm{V}_{\mathrm{CC}}=5.5 \mathrm{~V}$

DEVICE ORDERING INFORMATION

| Device Order <br> Number | Device Nomenclature |  |  |  |  |  |  |
| :--- | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Circuit <br> Indicator | Technology | Device <br> Function | Package <br> Suffix | Tape and Reel <br> Suffix | Package Type | Shipping $^{\dagger}$ |
| NLAST44599DT | NL | AS | 44599 | DT |  | TSSOP-16^ | 96 Unit / Rail |
| NLAST44599DTR2 | NL | AS | 44599 | DT | R2 | TSSOP-16^ | $2500 /$ Tape \& Reel |
| NLAST44599MN | NL | AS | 44599 | MN |  | QFN-16 | 124 Unit Rail |
| NLAST44599MNG | NL | AS | 44599 | MN |  | QFN-16 <br> (Pb-Free) | 124 Unit Rail |
| NLAST44599MNR2 | NL | AS | 44599 | MN | R2 | QFN-16 | $2500 /$ Tape \& Reel |
| NLAST44599MNR2G | NL | AS | 44599 | MN | R2 | QFN-16 <br> (Pb-Free) | $2500 /$ Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently $\mathrm{Pb}-$ Free.


QFN16 3x3, 0.5P
CASE 485G
ISSUE G
DATE 08 OCT 2021

side view

battam View

Nates:

1. DIMENSIDNING AND TDLERANCING PER ASME Y14.5M, 1994.
2. CDNTRZLLING DIMENSIDN: MILLIMETERS
3. DIMENSIDN b APPLIES TD PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FREM THE TERMINAL TIP.
4. CDPLANARITY APPLIES TD THE EXPOSED PAD AS WELL AS. THE TERMINALS.


DETAIL B
${ }^{\text {ALTERNATE }}$


DETAIL A
aLTERNATE TERMINAL
constructions

| DIM | MILLIMETERS |  |  |  |  |
| :--- | :--- | :--- | :--- | :---: | :---: |
|  | MIN. | NDM. | MAX. |  |  |
| A | 0.80 | 0.90 | 1.00 |  |  |
| A1 | 0.00 | 0.03 | 0.05 |  |  |
| A3 | 0.20 REF |  |  |  |  |
| b | 0.18 | 0.24 |  |  |  |
| D | 3.00 BSC |  |  |  |  |
| D2 | 1.65 | 1.75 |  |  | 1.85 |
| E | 3.00 BSC |  |  |  |  |
| E2 | 1.65 | 1.75 | 1.85 |  |  |
| e | 0.50 BSC |  |  |  |  |
| k | 0.18 TYP |  |  |  |  |
| L | 0.30 | 0.40 | 0.50 |  |  |
| L1 | 0.00 | 0.08 | 0.15 |  |  |

GENERIC MARKING DIAGRAM*

| ${ }^{\circ}$ XXXXX |
| :---: |
| XXXXX |
| ALYW: |
| $\bullet$ |

XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week

- = Pb-Free Package
(Note: Microdot may be in either location)
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-$ Free indicator, "G" or microdot " $\quad$ ", may or may not be present. Some products may not follow the Generic Marking.

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | QFN16 3X3, 0.5P | PAGE 1 OF 1 |



TSSOP-16
CASE 948F-01
ISSUE B
DATE 19 OCT 2006

SCALE 2:1


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